





DMG8601UFG

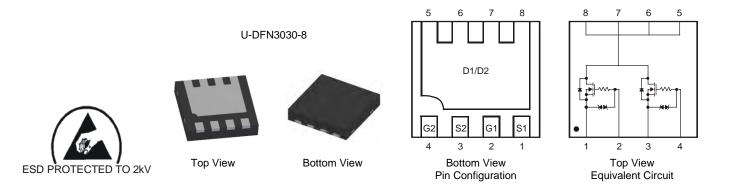
#### **DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

#### **Features**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 2KV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: U-DFN3030-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper lead frame. Solderable per MIL-STD-202, Method 208 <sup>♠</sup>
- Polarity: See Diagram
- Weight: 0.0172 grams (approximate)



### Ordering Information (Note 4)

Part Number	Case	Packaging	
DMG8601UFG-7	U-DFN3030-8	3000/Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

# **Marking Information**



2N4 = Product marking code YYWW = Date code marking YY = Last digit of year (ex: 09 for 2009) WW = Week code (01 to 53)



## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			VDSS	20	V
Gate-Source Voltage		Vgss	±12	V	
Continuous Drain Current (Note 5)	Steady State	TA = +25°C TA = +70°C	lo	6.1 5.2	А
Pulsed Drain Current		IDM	27	Α	

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	Pb	0.92	W
Thermal Resistance, Junction to Ambient @TA = +25°C	Røja	136	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

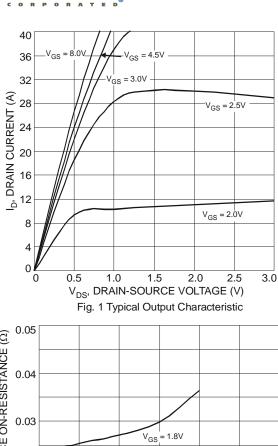
### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

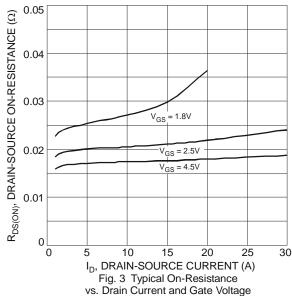
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = 25°C	I <sub>DSS</sub>	-	-	1.0	μА	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±10	μΑ	$V_{GS} = \pm 10V, V_{DS} = 0V$	
Gate-Source Breakdown Voltage	BV <sub>SGS</sub>	±12	-	-	V	$V_{DS} = 0V, I_{G} = \pm 250 \mu A$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.35	-	1.05	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
		-	17	23		$V_{GS} = 4.5V, I_D = 6.5A$	
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	-	20	27	$m\Omega$	$V_{GS} = 2.5V, I_D = 5.5A$	
	, ,	-	25	34		$V_{GS} = 1.8V, I_D = 3.5A$	
Forward Transfer Admittance	Y <sub>fs</sub>	-	10	-	S	$V_{DS} = 10V, I_{D} = 5A$	
Diode Forward Voltage	$V_{SD}$	-	0.7	1.0	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS							
Input Capacitance	C <sub>iss</sub>	-	143	-	pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V,	
Output Capacitance	Coss	-	74	-	pF		
Reverse Transfer Capacitance	Crss	-	29	-	pF	f = 1.0MHz	
Gate Resistance	$R_g$	-	202	-	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	Qq	-	8.8	-	nC		
Gate-Source Charge	Q <sub>gs</sub>	-	1.4	-	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_{D} = 6.5A$	
Gate-Drain Charge	Q <sub>qd</sub>	-	3.0	-	nC		
Turn-On Delay Time	t <sub>D(on)</sub>	-	53	-	ns		
Turn-On Rise Time	t <sub>r</sub>	-	78	-	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$ $R_L = 10\Omega, R_G = 6\Omega$	
Turn-Off Delay Time	t <sub>D(off)</sub>	-	562	-	ns		
Turn-Off Fall Time	t <sub>f</sub>	-	234	-	ns	]	

Notes:

- 5. Device mounted on FR-4 PCB with minimum recommended pad layout.
- 6. Short duration pulse test used to minimize self-heating effect.







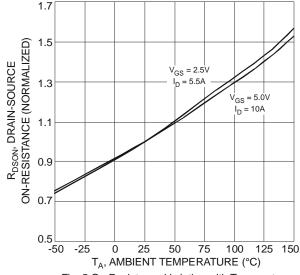
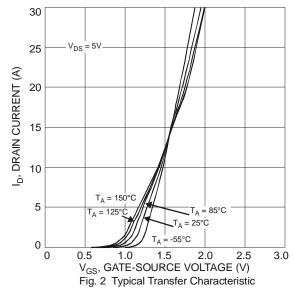
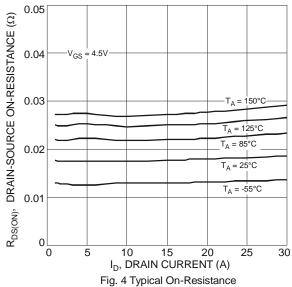


Fig. 5 On-Resistance Variation with Temperature





0.05  $R_{DSON}$  DRAIN-SOURCE ON-RESISTANCE  $(\Omega)$ 0.04 GS = 2.5 0.03  $I_{D} = 5.5A$ V<sub>GS</sub> = 5.0V I<sub>D</sub> = 10A 0.01 0 -50 -25 25 50 75 100 125 150 T<sub>A</sub>, AMBIENT TEMPERATURE (°C)

vs. Drain Current and Temperature

Fig. 6 On-Resistance Variation with Temperature



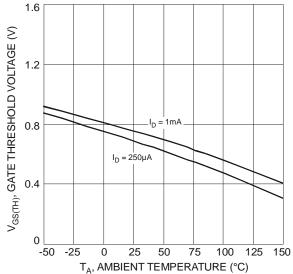


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

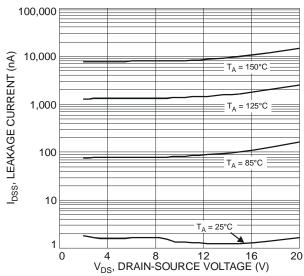


Fig. 9 Typical Leakage Current vs. Drain-Source Voltage

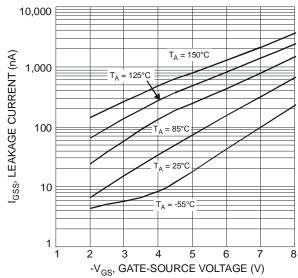
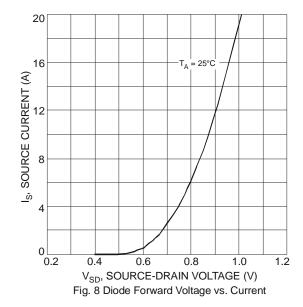
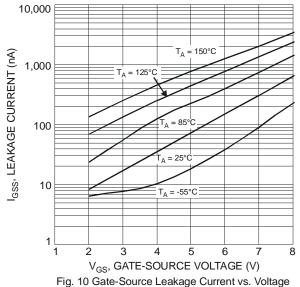


Fig. 11 Gate-Source Leakage Current vs. Voltage







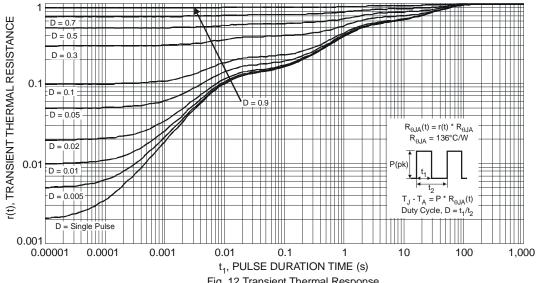
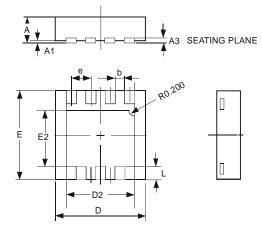


Fig. 12 Transient Thermal Response

# **Package Outline Dimensions**

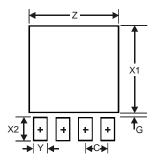
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



U-DFN3030-8					
Dim	Min	Max	Тур		
Α	0.57	0.63	0.60		
A1	0	0.05	0.02		
А3	_		0.15		
b	0.29	0.39	0.34		
D	2.90	3.10	3.00		
D2	2.19	2.39	2.29		
е	_		0.65		
Е	2.90	3.10	3.00		
E2	1.64	1.84	1.74		
L	0.30	0.60	0.45		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.59
G	0.11
X1	2.49
X2	0.65
Υ	0.39
С	0.65



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